

AMENDMENTS

In the Specification

Amend the Title as follows:

-- DRAM Circuitry, Method Of Forming A Field Emission Device, And Field Emission Device--

On page 1, after the title and prior to the "Technical Field", insert:

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/641,879 filed on August 17, 2000, which is a divisional application of U.S. Patent Application Serial No. 09/248,197 filed February 10, 1999.--

Please replace the Abstract Of The Disclosure with the following clean version in accordance with 37 C.F.R. §1.121(b)(1)(ii).

--The invention is DRAM circuitry, a method of forming a field emission device, and a field emission device. Depositing an aluminum nitride comprising layer over a substrate includes positioning a substrate within a chemical vapor deposition reactor. Ammonia and at least one of triethylaluminum and trimethylaluminum are fed to the reactor while the substrate is at a temperature of about 500°C or less and at a reactor pressure from about 100 mTorr to about 725 Torr effective to deposit a layer comprising aluminum nitride over the substrate at such temperature and reactor pressure. In one aspect, such layer is utilized as a cell dielectric layer in DRAM circuitry. Such layer is deposited over emitters of a field emission display. The invention contemplates DRAM and field emission devices utilizing such layer and alternate layers.--